

EAST - [10647700.wsp.1]

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Drafts
BRS: (phase-changeable)

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115: (105) ((phase-changeable) or (phas
116: (32) 115 and (germanium or stibium

Failed

Saved
(22) (phase-changeable near memory) or
(2) ("5814527").PN.
(22) (phase-changeable near memory) or
(1) "3423646".PN.
(1) "3796926".PN.
(1) "4099260".PN.
(1) "4115872".PN.
(22) (phase-changeable near memory) or
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(300) (phase-changeable) or (phase adj d
(105) ((phase-changeable) or (phase adj c

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DBs: USPAT; EPO; JPO; DERWENT; IBM; TDB

Plurals

Default operator: OR

Highlight all hit terms initially

115 and (germanium or stibium or tellurium)

BRST ID# Image Text HTML

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef |
|----|--------------------------|--------------------------|---------------|------------|-------|---|------------|------------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 6423621 B1 | 20020723 | 24 | Controllable ovonic phase-change semiconductor memory device and | 438/597 | 257/20; 257/3; |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 6329666 B1 | 20011211 | 24 | Controllable ovonic phase-change semiconductor memory device and | 257/3 | 257/4; 257/41; |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 6294452 B1 | 20010925 | 22 | Controllable ovonic phase-change semiconductor memory device and | 438/597 | 257/20; 257/529; |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 6150253 A | 20001121 | 24 | Controllable ovonic phase-change semiconductor memory device and | 438/597 | 257/E27.004; 257/E45.002; |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 6011757 A | 20000104 | 8 | Optical recording media having increased erasability | 369/13.35 | 428/64.1; 430/270.13 |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 5850378 A | 19981215 | 30 | Method and apparatus for recording data on an optical disk and or groove | 369/59.11 | 369/116; 369/275.3; |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 5596522 A | 19970121 | 35 | Homogeneous compositions of microcrystalline semiconductor material, | 365/113 | 257/3; 257/4; |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 5591501 A | 19970107 | 6 | Optical recording medium having a plurality of discrete phase change data recording | 428/64.1 | 369/275.1; 369/275.2; |
| 9 | <input type="checkbox"/> | <input type="checkbox"/> | US 5362538 A | 19941108 | 10 | Optical recording medium | 428/64.5 | 346/135.1; 347/264; |
| 10 | <input type="checkbox"/> | <input type="checkbox"/> | US 5335219 A | 19940802 | 37 | Homogeneous composition of microcrystalline semiconductor material, | 369/288 | 257/E27.004; 257/E27.103; |
| 11 | <input type="checkbox"/> | <input type="checkbox"/> | US 5128099 A | 19920707 | 12 | Congruent state changeable optical memory material and device | 420/579 | 148/304; 148/403; |